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MCKENNA LONG & ALDRIDGE LLP			CHOWDHURY, T.	CHOWDHURY, TARIFUR RASHID	
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Please find below and/or attached an Office communication concerning this application or proceeding.

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Paper No(s)/Mail Date

2) Motice of Draftsperson's Patent Drawing Review (PTO-948)

3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)

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6) Other: \_\_\_

5) Notice of Informal Patent Application (PTO-152)

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#### **DETAILED ACTION**

## Claim Rejections - 35 USC § 103

- 1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
  - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 2. This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CER\_1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(e), (f) or (g) prior art under 35 U.S.C. 103(a).
- 3. Claims 1-32 are rejected under 35 U.S.C. 103(a) as being unpatentable over Kim, USPAT 6,043,511 in view of Choi et al., (Choi), US 2002/0117691
- 4. Kim discloses and shows in Figs. 9-11 and 13A-13C, an array substrate for use in a liquid crystal display device, comprising:
- a gate electrode (12), a gate line (11) and a gate pad electrode (13) on a substrate (100), wherein all of the gate electrode, the gate line and the gate pad electrode have a double-layered structure including a first and second layers formed by AL-Nd and Mo, or Cr (first barrier metal layer) and Al-Nd (Fig. 13A; col. 6, lines 19-60);

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- a gate insulating layer (20) on the substrate covering the double-layered gate electrode, gate line and gate pad (Fig. 13A);

- an active layer (30) and an ohmic contact layer (40) sequentially formed on the gate insulating layer and over the gate electrode;
- a data line (51) on the gate insulating layer crossing the gate line (11), source and drain electrodes (52, 53) contacting the ohmic contact layer (40), and a data pad electrode (54) on the gate insulating layer (Fig. 13B);
- a passivation layer (60)formed on the gate insulating layer to cover the data line, source and drain electrodes and data pad electrode, wherein the passivation layer has a drain contact hole exposing the drain electrode (53), a gate pad contact hole exposing the gate pad electrode (13), and a data pad contact hole exposing the data pad (54) (Fig. 13C); and

- a pixel electrode (70), a gate pad terminal and a data pad terminal all of which are formed of a transparent conductive material on the passivation layer (col. 7, lines 18-21).

As discussed above Kim discloses that the gate electrode, gate line and gate pad electrode have double-layered structure including a first barrier metal layer and a first layer of Al-Nd. Kim differs from the instant invention because he does not explicitly disclose the limitations such as (1) the gate electrode, the gate line and the gate pad electrode have a double-layered structure wherein the first layer is copper and (2) the data line, the source and drain electrodes and the data pad electrode having a double-layered structure including a second barrier metal layer and a second copper layer.

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Choi discloses an array substrate for use in a liquid crystal display device wherein the gate line assembly (including gate line, gate electrode and gate pad) and the data line assembly (includes data line, source electrode, drain electrode and data pad) can be formed of a double-layered structure such as a barrier metal layer and a copper layer. Choi also discloses that copper has low resistance( page 8, paragraph 0118; page 9, paragraph 0125, 0129, 0132-0135; page 10, paragraph 0148; page 11, paragraph 0152).

Choi is evidence that ordinary workers in the art would find a reason, suggestion or motivation to use copper to form gate line assembly and data line assembly.

Therefore, it would have been obvious to one of ordinary skill in the art at the time of the invention was made to substitute the Al-Nd layer of the gate electrode, the gate line, the gate pad, the data line, the drain electrode, the source electrode and the data pad electrode of Kim with a copper layer for advantages such as to obtain low resistance wiring, as per the teachings of Choi.

Accordingly, claim 1 would have been obvious.

As to claim 17, the method of forming the array substrate for use in a liquid crystal display device merely recites the steps of forming each element and since each element must be formed to make the device, the method would have at least been obvious.

As to claims 2, 3, 18 and 19, Kim shows in Fig. 9 that the gate electrode (12) extends from the gate line (11) and the gate electrode is at the end of the gate line and that the source electrode (52) extends from the data line (51), wherein the drain

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electrode (53) is spaced apart from the source electrode, and wherein the data pad (54) is at the end of the data line (51).

As to claims 4 and 20, Figs. 9 and 13C of Kim also shows that the pixel electrode (70) is disposed in a pixel region defined by the crossing of the gate and data lines, wherein the pixel electrode contacts the drain electrode (53) through the drain contact hole, wherein the gate pad terminal contacts the gate pad through the gate pad contact hole (14) and wherein the data pad terminal contacts the data pad through the data pad contact hole (55).

As to claims 5-8 and 21-24, Kim discloses that the barrier metal layer is chromium, which inherently has good adhesive characteristics (col. 6, lines 56-60).

As to claims 9, 10, 25 and 26, Choi discloses (page 6, paragraph 0091) and shows in Fig. 7, a double-layered capacitor electrode on the gate insulating layer and over the portion of the gate line, wherein the double-layered capacitor electrode is connected in parallel with the pixel electrode through a contact hole that formed in the passivation layer and thus would have been obvious to form storage capacitance for improving storage capacity of the pixel electrode.

As to claims 11 and 27, Kim discloses (col. 4, lines 66-67) that the gate insulation layer is an inorganic material such as silicon oxide or silicon nitride.

As to claims 12 and 28, Kim further discloses (col. 5, lines 14-15) that the passivation layer is made of silicon nitride.

As to claims 13-16 and 29-32, Choi discloses the use of a buffer layer (page 9, paragraph 0131) made of an inorganic material to separate the gate line assembly from

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the substrate and data line assembly form the thin film transistor array to prevent contacts between the substrate and the barrier metal layer as well as the contacts between the barrier metal layer and the thin film transistor array and thus would have been obvious.

## Response to Arguments

5. Applicant's arguments, see remarks and English translation of the priority document filed on 01/21/05, with respect to the rejection(s)of claim(s) 1-8,11-24,27-32 under 35 U.S.C 102(e) have been fully considered and are persuasive. Therefore, the rejection has been withdrawn. However, upon further consideration, a new ground(s) of rejection is made under 35 U.S.C 103 OVER Kim in view of Choi.

#### Conclusion

6. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Tarifur R. Chowdhury whose telephone number is (571) 272-2287. The examiner can normally be reached on M-Th (6:30-5:00) Friday Off.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Robert Kim can be reached on (571) 272-2293. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

TRC April 06, 2005

ARIFUR R. CHOWDHURY-

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